



DMN4030LK3

Product Summary

BVDSS	Rds(on)	ID TA = +25°C
401/	30mΩ @V _{GS} = 10V	9.6A
40V	$50m\Omega @V_{GS} = 4.5V$	7.4A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- **DC-DC Converters**
- **Power Management Functions**

40V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

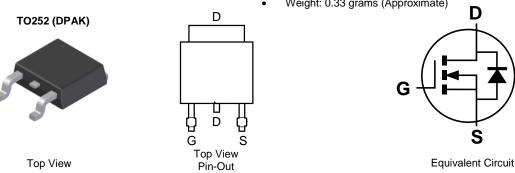
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts gualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-

products/.

- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/guality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMN4030LK3Q)

Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN4030LK3-13	TO252 (DPAK)	2,500/Tape & Reel

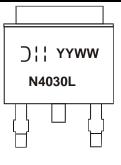
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



∃:: = Manufacturer's Marking N4030L = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 21 = 2021) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	Vdss	40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 5) $V_{GS} = 10V$	lo	9.6 7.7	A		
Maximum Body Diode Continuous Current (Note 5)		ls	9.6	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			Ідм	37.7	А
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			Ism	37.7	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	4.18	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	29.9	°C/W
Total Power Dissipation (Note 7)	T _A = +25°C	PD	2.14	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R _{0JA}	58.4	°C/W
Thermal Resistance, Junction to Case (Note 8)		R _{0JC}	2.46	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	•						
Drain-Source Breakdown Voltage	BVDSS	40		—	V	Vgs = 0V, Id = 250µA	
Zero Gate Voltage Drain Current	IDSS	_		1	μA	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	lgss			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(th)	1		3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Basisti	_	21	30	mΩ	VGS = 10V, ID = 12A	
	R _{DS(ON)}	_	37	50	11122	$V_{GS} = 4.5V, I_{D} = 6A$	
Diode Forward Voltage	Vsd		0.95	1.1	V	V _{GS} = 0V, I _S = 12A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	604	_			
Output Capacitance	Coss	_	106	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	59.6	_			
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	6.5	—			
Total Gate Charge (V _{GS} = 10V)	Qg		12.9	_	nC		
Gate-Source Charge	Qgs	_	2.3	_	nc	$V_{DS} = 20V, I_D = 12A$	
Gate-Drain Charge	Q _{gd}	_	3.6	—			
Turn-On Delay Time	t _{D(ON)}	_	4.2	_			
Turn-On Rise Time	tR	_	12.4	_		V _{DD} = 20V, I _D = 12A	
Turn-Off Delay Time	tD(OFF)	_	13.8	_	ns	$V_{GS} = 10V, R_G = 6\Omega$	
Turn-Off Fall Time	tF	_	10.7				
Body Diode Reverse Recovery Time	trr	_	135		ns	IF = 12A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	QRR	_	799		nC	IF = 12A, di/dt = 100A/µs	

Notes: 5. For a device surface mounted on 50mm x 50mm x 1.6mm FR-4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as note 5, except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature. 7. For a device surface mounted on 25mm x 25mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is

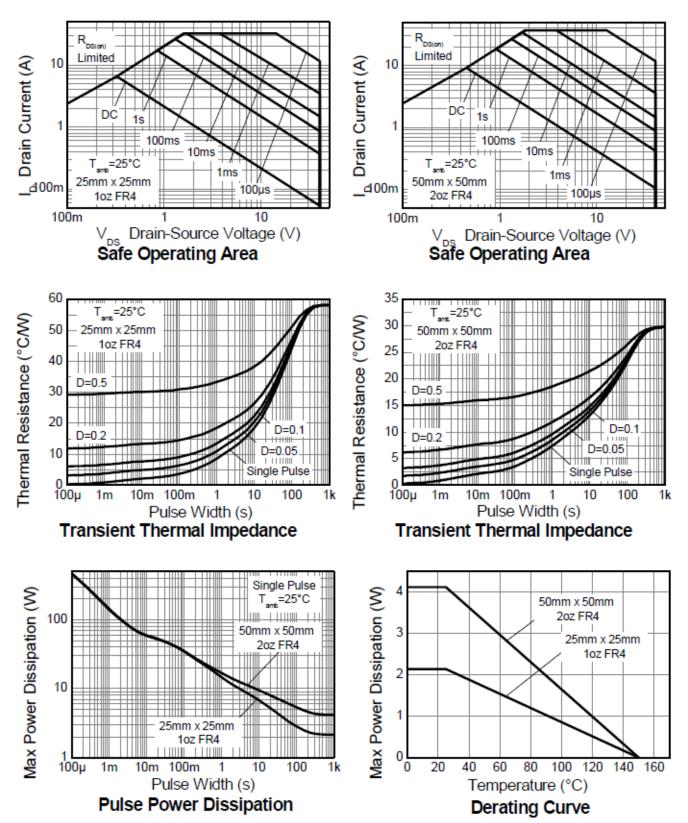
measured when operating in a steady-state condition.

8. Thermal resistance from junction to solder-point (at the end of the drain lead).

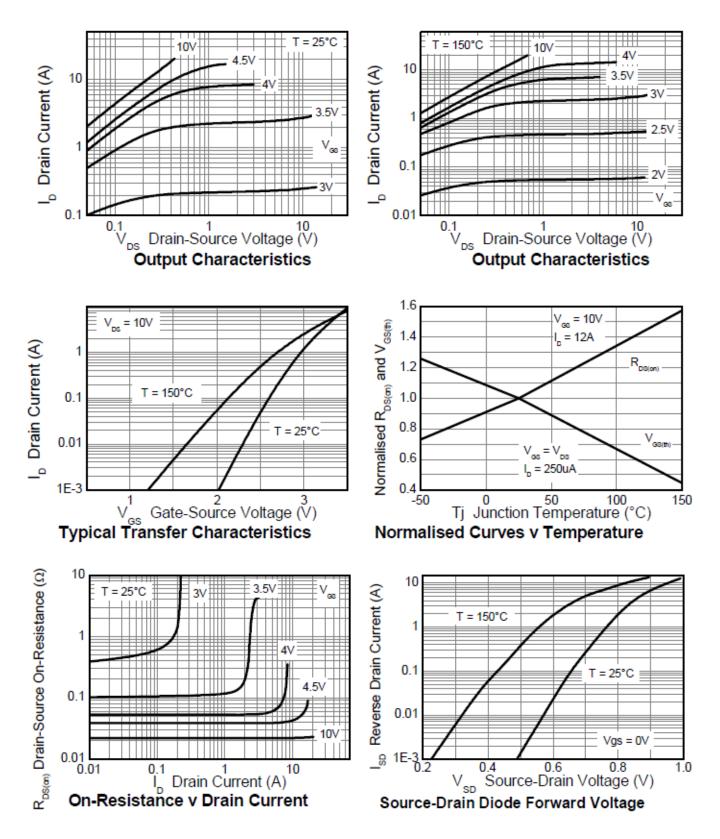
9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

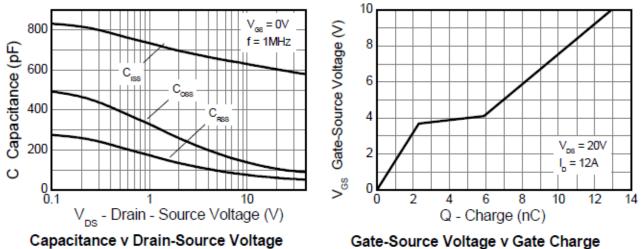










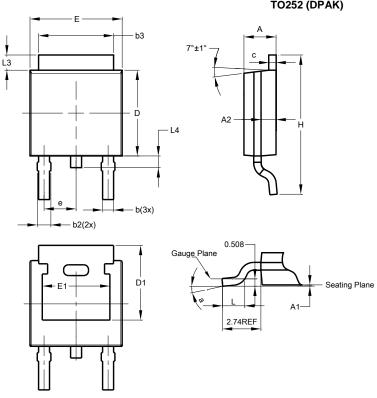


Gate-Source Voltage v Gate Charge



Package Outline Dimensions

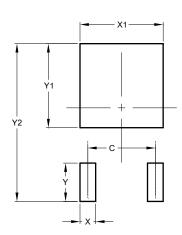
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е			2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

TO252 (DPAK)



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